TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT Process)

2SA1452A

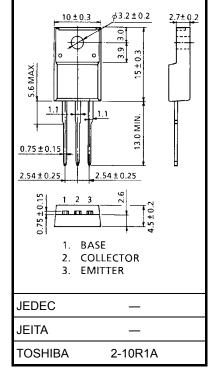
High-Speed, High-Current Switching Applications

Unit: mm

- Low collector saturation voltage: V_{CE} (sat) = -0.4 V (max) (I_{C} = -6 A)
- High-speed switching: $t_{stg} = 1.0 \mu s$ (typ.)
- Complementary to 2SC3710A

Absolute Maximum Ratings (Tc = 25°C)

| Characteristics | Symbol | Rating | Unit |
|-----------------------------------------|------------------|------------|------|
| Collector-base voltage | V _{CBO} | -80 | V |
| Collector-emitter voltage | V _{CEO} | -80 | V |
| Emitter-base voltage | V _{EBO} | -6 | V |
| Collector current | Ic | -12 | Α |
| Base current | Ι _Β | -2 | Α |
| Collector power dissipation (Tc = 25°C) | PC | 30 | W |
| Junction temperature | Tj | 150 | °C |
| Storage temperature range | T _{stg} | -55 to 150 | °C |



Weight: 1.7 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the

reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

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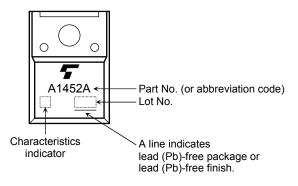


Electrical Characteristics (Tc = 25°C)

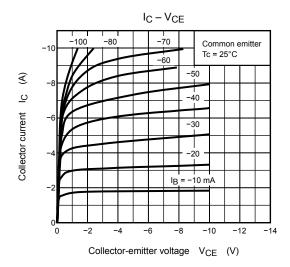
| Chara | acteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|-----------------------------------------|----------------------------|------------------------------------------------------------------------------|---------------------------------------------------------------------------------|-----|------|------|------|
| Collector cut-off of | current | I _{CBO} | $V_{CB} = -80 \text{ V}, I_E = 0$ | _ | _ | -10 | μA |
| Emitter cut-off cu | rrent | I _{EBO} | V _{EB} = -6 V, I _C = 0 | | _ | -10 | μA |
| Collector-emitter | breakdown voltage | V (BR) CEO | $I_C = -50 \text{ mA}, I_B = 0$ | -80 | _ | _ | V |
| DC current gain | h _{FE (1)} (Note) | V _{CE} = -1 V, I _C = -1 A | 70 | _ | 240 | | |
| | | h _{FE} (2) | V _{CE} = -1 V, I _C = -6 A | 40 | _ | _ | |
| Collector-emitter | saturation voltage | V _{CE} (sat) | I _C = -6 A, I _B = -0.3 A | _ | -0.2 | -0.4 | V |
| Base-emitter satu | uration voltage | V _{BE} (sat) | I _C = -6 A, I _B = -0.3 A | _ | -0.9 | -1.2 | v |
| Transition freque | ncy | f _T | V _{CE} = -5 V, I _C = -1 A | _ | 50 | _ | MHz |
| Collector output of | capacitance | C _{ob} | V _{CB} = -10 V, I _E = 0, f = 1 MHz | _ | 400 | _ | pF |
| Switching time Storage time Fall time | t _{on} | 20 µs Input B2 Output 20 µs Input B2 G G G G G G G G G G G G G | _ | 0.3 | _ | | |
| | t _{stg} | | _ | 1.0 | _ | μs | |
| | Fall time | t _f | V_{CC} ≈ -30 V -I _{B1} = I _{B2} = 0.3 A, duty cycle ≤ 1% | _ | 0.5 | _ | |

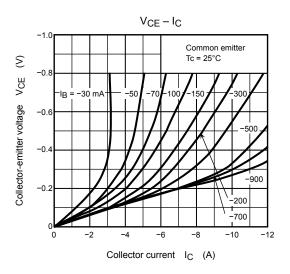
Note: h_{FE} (1) classification O: 70 to 140, Y: 120 to 240

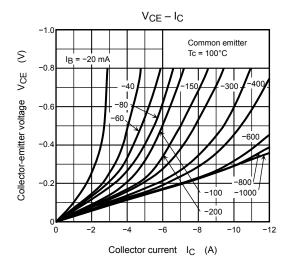
Marking

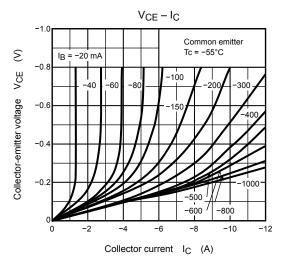


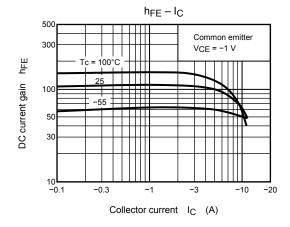
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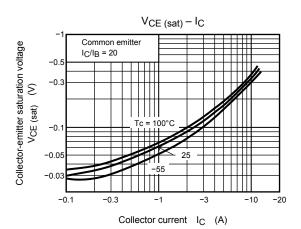




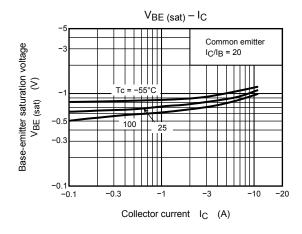


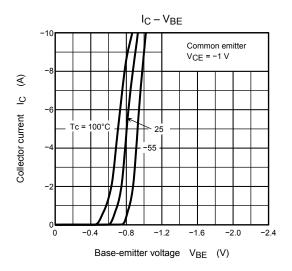


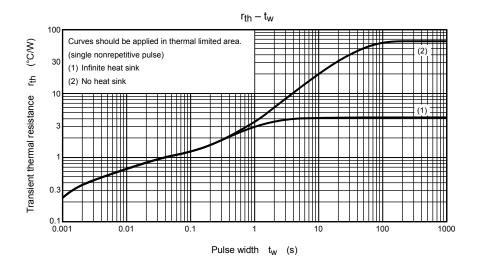




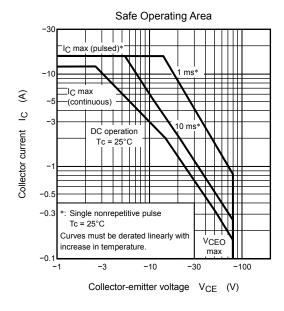
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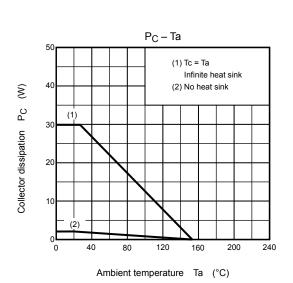






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